## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Application No.:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

For: TRANSFER OF A THIN LAYER FROM A

Attorney Docket No.: 4717-7600

WAFER COMPRISING A BUFFER LAYER

## INFORMATION DISCLOSURE STATEMENT

## MS PATENT APPLICATION

Commissioner for Patents Washington, D.C. 20231

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of twelve (12) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the International Search Report from the French priority application on which some of the references were cited. It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the these references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 501-814.

Respectfully submitted,

July 8, 2003

E. Bradley Gould

(Reg. No. 41,792)

For: Allan A. Fanucci

(Reg. No. 30,256)

WINSTON & STRAWN Customer No. 28765

202-371-5771

LIS	T OF	REFERENCES CIT	ATTY. DOCKET NO.:		APPLICATION NO.:				
Form PTO-1449 (Use several sheets if necessary)  Sheet 1 of 1					4717-7600 APPLICANT:	<u> </u>			
					Bruno GHYSELEN et al. FILING DATE: GROUP:				
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*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING APPRO	DATE IF
-	A	6,573,126	06/2003	Cheng et al.		438	149	149	
	В	6,524,935	02/2003	Canaperi et al.  Yu et al.  Maleville et al.  Kub et al.  Chu et al.		438	478		
	С	6,410,371	06/2002			438	151		
	D	6,403,450	06/2002			438	471		
	Е	6,323,108	11/2001			438	458		
	F	6,059,895	05/2000			148	33.1		
	G	5,882,987	03/1999	Srikrishnan		438	458		
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		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUBCLASS	TRANSI YES	NO NO
	Н	02/33746	04/2002	wo					
	I	2 365 214	02/2002	Great Britain WO			1		
	J	01/99169	12/2001						
	K	01/11930	02/2001	wo					
		OTHER REFER	ENCES (Inc	cluding Author,	Title, Date, Pertinent	Pages, Etc.	)		
L.J. Huang et al., SiGe-On-Insulator Prepared by Wafer Bonding and Layer Transfer for High Performance Field-Effect Transistors, Applied Physics Letters, February 26, 2002, Vol 78, No. 9									
EXAMINER DATE CONSIDERED									
*EXAMINI conformance		Initial if reference considered to considered. Include copy				9. Draw line	through cita	tion if	not in